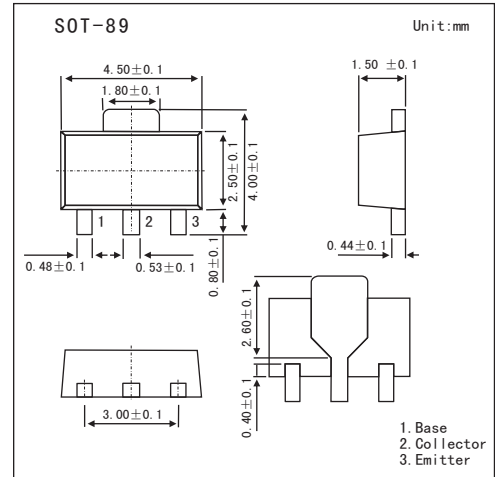


PNP Silicon Epitaxial Transistor

KTA1273

■ Features

- Collector Power Dissipation: $P_c=500\text{mW}$
- Collector current: $I_c=-2\text{A}$
- Complementary to KTC3205



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-30	V
Collector to emitter voltage	V_{CEO}	-30	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current (DC)	I_c	-2	A
Collector Power Dissipation	P_c	500	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c = -1\text{mA}, I_E = 0$	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c = -10\text{mA}, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}, I_c = 0$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -30\text{V}, I_E = 0\text{A}$			-0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5\text{V}, I_c = 0\text{A}$			-0.1	μA
DC current gain *	h_{FE}	$V_{CE} = -2\text{V}, I_c = -500\text{mA}$	100		320	
Collector saturation voltage	$V_{CE(sat)}$	$I_c = -1.5\text{A}, I_B = -30\text{mA}$			-2	V
Base to emitter voltage	V_{BE}	$V_{CE} = -2\text{V}, I_c = -500\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -2\text{V}, I_E = 500\text{mA}$		120		MHz
Output capacitance	C_{ob}	$V_{CE} = -10\text{V}, I_E = 0, f = 1.0\text{MHz}$		48		pF

* Pulsed: $PW \leq 350\ \mu\text{s}$, Duty Cycle $\leq 2\%$

■ h_{FE} Classification

Rank	O	Y
Range	100~200	160~320